

UNISONIC TECHNOLOGIES CO., LTD

UG10N120

Preliminary

Insulated Gate Bipolar Transistor

35A, 1200V NPT SERIES N-CHANNEL IGBT

DESCRIPTION

The UTC **UG10N120** is a NPT series N-Channel IGBT, it uses UTC's advanced technology to provide the customers with a minimum on-state resistance, etc.

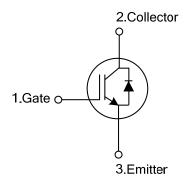
The UTC **UG10N120** is suitable for AC and DC motor controls, power supplies, and drivers for solenoids, relays and contactors, etc.

FEATURES

* Low conduction loss

* Short circuit rating

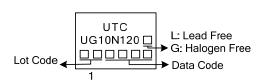
SYMBOL

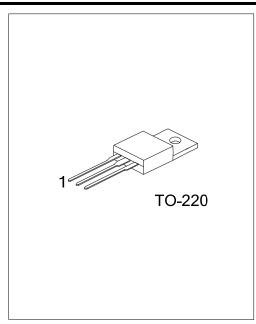


ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Dooking	
Lead Free	Halogen Free	Fackage	1	2	3	Packing	
UG10N120L-TA3-T	UG10N120G-TA3-T	TO-220	G	С	Е	Tube	
Note: Pin Assignment: G: Gate C: Collector E: Emitter							
UG10N120L- <u>TA3-T</u>	(1) T: Tube (2) TA3: TO-220 (3) L: Lead Free,	G: Halo	gen Free	e and Le	ad Free		

MARKING





■ ABSOLUTE MAXIMUM RATING (T_c=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector to Emitter Voltage		V _{CES}	1200	V
Gate-Emitter Voltage		V _{GES}	±20	V
Gate to Emitter Voltage Pulsed		V _{GEM}	±30	V
Collector Current Continuous	T _C =25°C	1	35	А
	T _C =110°C	l _C	17	А
Collector Current Pulsed (Note 1)		I _{СМ}	80	А
Power Dissipation Total at $T_c = 25^{\circ}C$		P _D	298	W
Power Dissipation Derating $T_c > 25^{\circ}C$			2.38	W/°C
Forward Voltage Avalanche Energy (Note 2)		E _{AV}	80	mJ
Short Circuit Withstand Time (Note 3) at V _{GE} =15V		t _{sc}	8	μs
Short Circuit Withstand Time (Note 3) at V _{GE} =12V		t _{sc}	15	μs
Operating Junction Temperature Range		ΤJ	-55~+150	°C
Storage Temperature Range		T _{STG}	-55~+150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Pulse width limited by maximum junction temperature.

- 3. I_{CE} =20A, L=400µH, T_J=25°C.
- 4. $V_{CE(PK)}$ =840V, T_J =125°C, R_G =10 Ω .

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Case	θ _{JC}	0.42	°C/W	

■ **ELECTRICAL CHARACTERISTICS** (T_C=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
Collector to Emitter Breakdown Voltage	BV _{CES}	I _C =250µA, V _{GE} =0V		1200			V
Emitter to Collector Breakdown Voltage	BV _{ECS}	I _C =10mA, V _{GE} =0V		15			V
Collector to Emitter Leakage Current	I _{CES}	V _{CE} =1200V	T _C =25°C			250	μA
			T _C =125°C		150		μA
			T _C =150°C			2	mA
Collector to Emitter Saturation Voltage	V _{CE(SAT)}	I _C =10A, V _{GE} =15V	T _C =25°C		2.45	2.7	V
			T _C =150°C		3.7	4.2	V
Gate to Emitter Threshold Voltage	V _{GE(TH)}	I _C =90µA, V _{CE} =V _{GE}		6.0	6.8		V
Gate to Emitter Leakage Current	I _{GES}	V _{GE} =±20V				±250	nA
Switching SOA	SSOA	T _J =150°C, R _G =10Ω, V _{GE} =15V, L=400μH, V _{CE(PK)} =1200V		55			А
Gate to Emitter Plateau Voltage	V_{GEP}	I _C =10A, V _{CE} =600V			10.4		V
On-State Gate Charge	Q _{G(ON)}	I _C =10A, V _{CE} =600V	V _{GE} =15V		100	120	nC
			V _{GE} =20V		130	150	nC
Current Turn-On Delay Time	t _{d(ON)}	IGBT and Diode at T _J =25°C I_{CE} =1A, V _{CE} =30V, V _{GE} =15V, R_{G} =10 Ω			250		ns
Current Rise Time	t _{rl}				400		ns
Current Turn-Off Delay Time	t _{d(OFF)}				275		ns
Current Fall Time	t _{fl}				165		ns



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